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PATENT APPLICATION 3/28/3
Purley

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q58705

Yoji OKAZAKI, et al.

Appln. No.: 09/659,456

Group Art Unit: 2815

Confirmation No.: 5835

Examiner: Joseph H. Nguyen

Filed: September 11, 2000

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For: LASER APPARATUS IN WHICH GaN-BASED COMPOUND SURFACE-EMITTING SEMICONDUCTOR ELEMENT IS EXCITED WITH GaN-BASED COMPOUND SEMICONDUCTOR LASER ELEMENT

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated December 20, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Claims 55-58 are added as new claims:

55. (New) A laser apparatus according to claim 1, wherein the semiconductor laser element is a broad area type semiconductor laser element having output power substantially in a range of 1 to 10 watts and the laser apparatus generates output power up to several watts in a stable fundamental transverse mode.

56. (New) A laser apparatus according to claim 28, wherein the semiconductor laser element is a broad area type semiconductor laser element having output power substantially in a